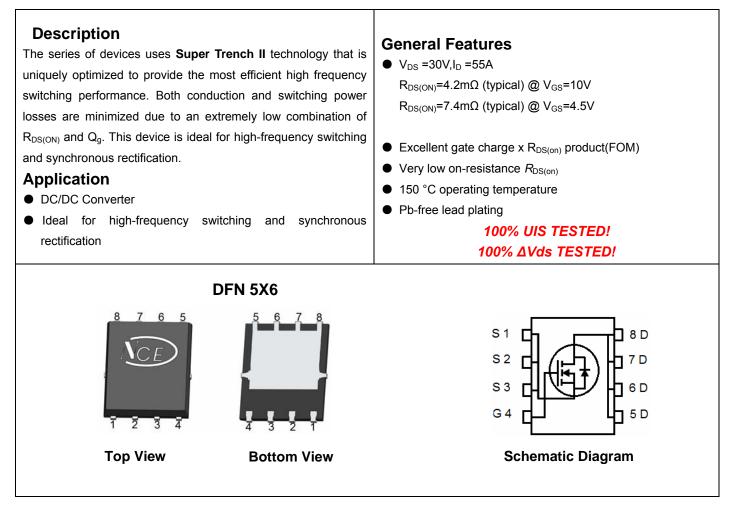


## NCE N-Channel Super Trench II Power MOSFET



#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P055N30GU	NCEP055N30GU	DFN5X6-8L	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	30	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Drain Current-Continuous	Ι <sub>D</sub>	55	А	
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	42	А	
Pulsed Drain Current	I <sub>DM</sub>	220	А	
Maximum Power Dissipation	PD	30	W	
Derating factor		0.24	W/℃	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	115	mJ	
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C	



#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	4.17	°C <b>/W</b>
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#### Electrical Characteristics (T<sub>C</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	iiiiii					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	iiiiii					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.6	2.0	V
Drain-Source On-State Resistance	P	V <sub>GS</sub> =10V, I <sub>D</sub> =27.5A	-	4.2	5.5	mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =27.5A	-	7.4	9.0	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =27.5A		30	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>Iss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,	-	980	-	PF
Output Capacitance	C <sub>oss</sub>		-	600	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	40	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	4	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =15V,I <sub>D</sub> =27.5A V <sub>GS</sub> =10V,R <sub>G</sub> =1.6Ω	-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg		-	9.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =15V,I <sub>D</sub> =27.5A,	-	3.2		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	3.0		nC
Drain-Source Diode Characteristics	i i					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =27.5A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	55	А
Reverse Recovery Time	t <sub>rr</sub>	$T_J$ = 25°C, $I_F$ = $I_S$	-	11	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	19	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

3. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25  $^\circ C$  ,V\_DD=20V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$ 

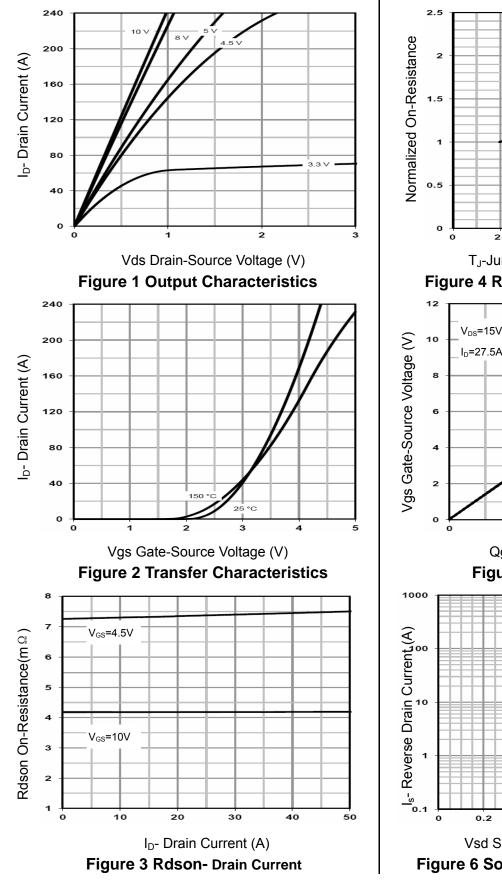


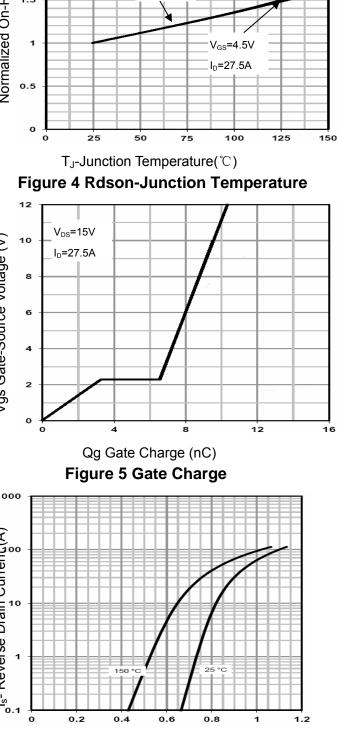
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V<sub>GS</sub>=10V

I<sub>D</sub>=27.5A





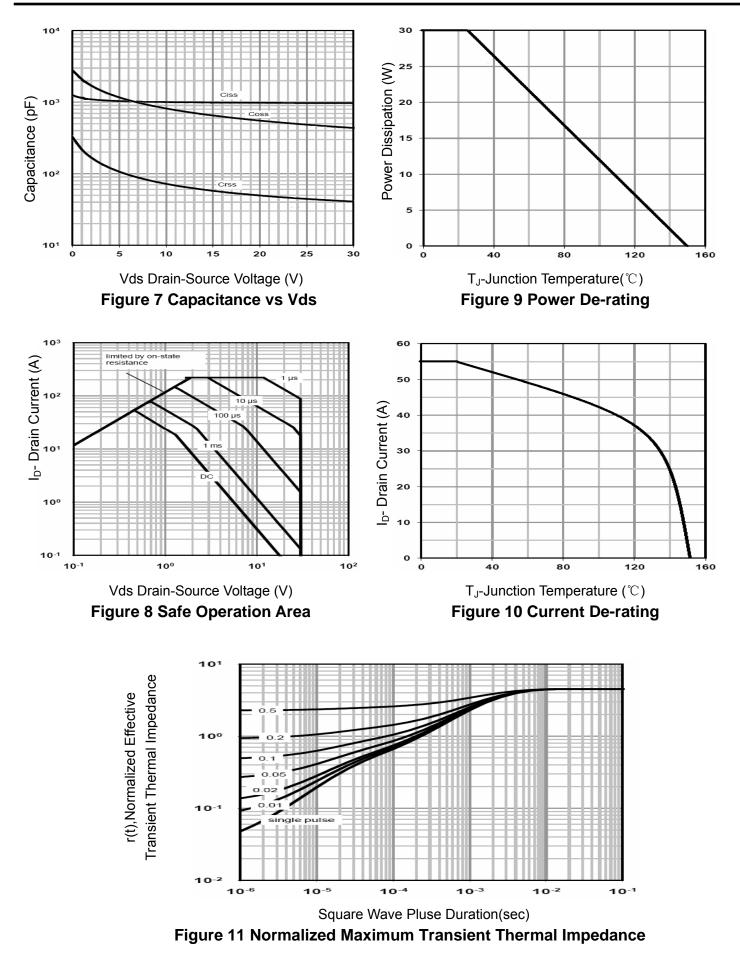


Vsd Source-Drain Voltage (V) Figure 6 Source- Drain Diode Forward



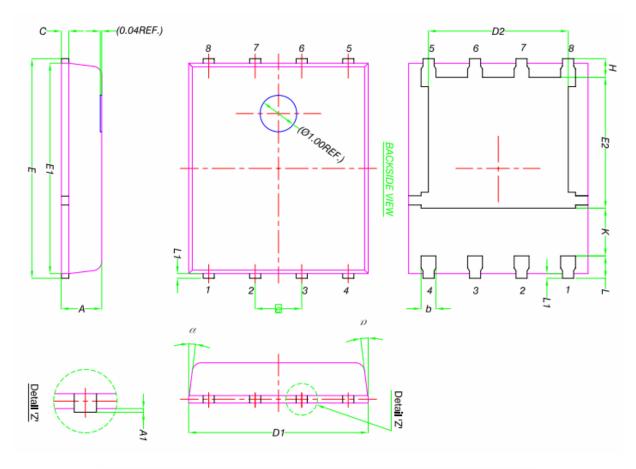
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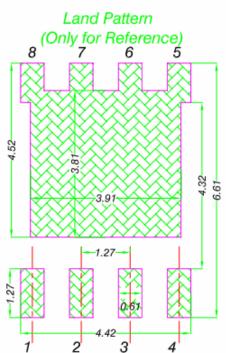




### DFN5X6-8L Package Information



	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	
А	0.90	1.00	1.10	
A1	0	-	0.05	
b	0.33	0.41	0.51	
С	0.20 0.25		0.30	
D1	4.80	4.90	5.00	
D2	3.61	3.81	3.96	
E	5.90	6.00	6.10	
E1	5.70	5.75	5.80	
E2	3.38	3.58	3.78	
е	1.27 BSC			
Н	0.41	0.51	0.61	
К	1.10	-	-	
L	0.51	0.61	0.71	
L1	0.06	0.13	0.20	
α	0°	-	12°	





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